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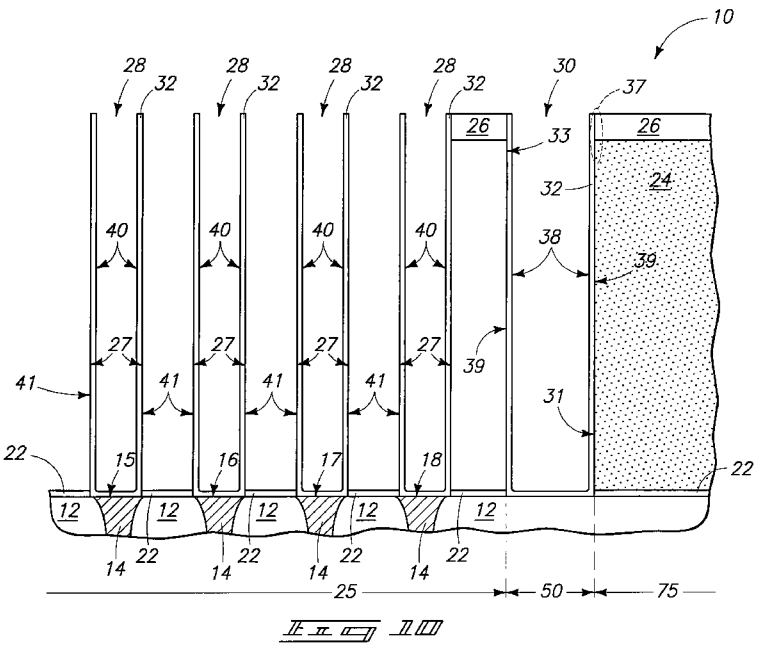
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(54) **Title**: METHODS OF FORMING A PLURALITY OF CAPACITORS



Фиг. 1

(57) **Abstract**: A method of forming a plurality of capacitors includes an insulative material received over a capacitor array area and a circuitry area. The array area comprises a plurality of capacitor electrode openings within the insulative material received over individual capacitor storage node locations. The intervening area comprises a trench. Conductive material is formed within the openings and against a sidewall portion of the trench to less than completely fill the trench. Covering material is formed over an elevationally outer lateral interface of the conductive material within the trench and the insulative material of the circuitry area. The insulative material within the array area is etched with a liquid etching solution effective to expose outer sidewall portions of the conductive material within the array area and to expose the conductive material within the trench. The conductive material within the array area is incorporated into a plurality of capacitors.

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